Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	236	("Si.sub.1-x" adj "Ge.sub.x") and (SiN (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:33
L2	11	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (SiN (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:47
L3	2	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (TiN (titanium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR:	OFF	2005/10/06 08:48
L4	0	(("Si.sub.0.5" adj "Ge.sub.0.5") same relaxed same graded) and (SiN (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:49
L5	28	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (etch-stop (etch adj stop) mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:59
L6	0	(("Si.sub.1-x" adj "Ge.sub.x") same relaxed same graded) and (etch adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 08:59
S1	2	"6689211".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/16 17:24
S2	2	"6521041".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/11 13:49

S3	176	(("20010003364") or ("20010007789") or	US-PGPUB; USPAT	OR	OFF	2004/12/17 12:30
		("20010007789") or	03/71			
		("20020043000") or				
		("20020084000") or			1	
		(20020096717) or ("20020100942") or				
		("20020123167") or				
		("20020123183") or				
		("20020125471") or				
		("20020168864") or				
		("20030003679") or				
		("20030013305") or			,	
	-	("20030034529") or				
		("20030057439") or	•	٠.		
		("20030102498") or				
		("20030119280") or				
		("20030127646") or				
		("20030139000") or				
		("20030157787") or				
		("20030137767") or				
		("20030180300") or				
		("20030189229") or				
		("20030199126") or				
		("20030201458") or				
		("20030203600") or				
		("20030207127") or				
		("20030215990") or			1	
		("20030218189") or				
		("20030219957") or				
		("20030227036") or				
		("20030227057") or				
		("20030230778") or				
		("20030232467") or				
		("20040005740") or				
/ /		("20040003740") or				
'		("20040007724") or				
		("20040012037") or				
		("20040012075") or				
		("20040014304") or				
		("20040018699") or				
		("20040031979") or				
		("20040031990") or	1			
		("20040041174") or				
		("20040041210") or				
		("20040048091") or				
		("20040048454") or				
		("20040051140") or				
	-	("20040053477") or				
		("20040075149") or ("4704302") or				
		("4710788") or ("4987462") or				
		("4990979") or ("4997776") or				
		("5155571") or ("5177583") or				
		("5240876") or ("5241197") or				
					-	
		("5250445") or ("5291439") or				
		("5298452") or ("5316958") or				
		("5399522") or ("5424243") or				
		("5426069") or ("5426316") or				
Coaret	History 10'C	("5439843") or ("5461250") or			-	
	History 10/6	/05-18479:0534Y or Pags 23243") or	1000000	1		
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1	1	("5617351") or ("5630905") or	1	}		
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S4	0	("'Si.sub.'\$" adj "'Ge.sub.'\$") same (etch etch-stop) same relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/17 12:31
S5	7	(("'Si.sub.1-x'" adj "'Ge.sub.x'")("'Si. sub.1-y'" adj "'Ge.sub.y'")("'Si.sub. 1-z'" adj "'Ge.sub.z'")) same (etch etch-stop) same relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/17 12:34
S6	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "Ge.sub.?""))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:20
S7	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'") not (silicon adj Nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:40
S8	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'") not (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:45
S9	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "Ge.sub.?"") not near2 (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:46
S10	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "Ge.sub.?") not (silicon adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:52
S11	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?" adj "Ge.sub.?"") not nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:53
S12	3315	(etch-stop (etch adj stop) (etch adj barrier)) near3 (silicon Si ("Si.sub. 1-?'" adj "'Ge.sub.?'") not nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:52
S13	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("Si.sub. 1-?'" adj "'Ge.sub.?'") not near3 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 10:53

S14	2106	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'") not near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 11:02
S15	169	(etch-stop (etch adj stop) (etch adj barrier)) near2 (silicon Si ("'Si.sub. 1-?'" adj "'Ge.sub.?'")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:42
S16	3	(etch-stop (etch adj stop) (etch adj barrier)) near2 (("'Si.sub.1-x'" adj "'Ge.sub.x'")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:44
S17	2	(etch-stop (etch adj stop) (etch adj barrier)) near2 (("Si.sub.1-y" adj "Ge.sub.y")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:45
S18	1	(etch-stop (etch adj stop) (etch adj barrier)) near2 (("'Si.sub.1-z'" adj "'Ge.sub.z'")) with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/12 14:45
S19	291	(etch adj stop) near2 (silicon adj dioxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:22
S20	4	(etch adj stop) near2 (silicon adj dioxide) with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:27
S21	0	(etch adj stop) near2 "'SiO.sub.2'" with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:27
S22	0	(etch adj stop) near2 SiO with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:27
S23	0	(etch adj stop) near2 (Silicon adj oxide) with relaxed	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 09:28

S24	33	("'Si.sub.1-x'" adj "'Ge.sub.x'") with relaxed with graded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 10:30
S25	12	(("2002140031") or ("2003003679") or ("5013681") or ("5548128") or ("5607876") or ("5906951") or ("6154475") or ("6372593") or ("6489639") or ("6521041") or ("6591321") or ("6597016") or ("6674150") or ("6689211")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/05 16:30